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Supporting Information

Site-controlled single photon emitters fabricated by near field illumination

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1. Calculation of QD diameter

Using the emission energies in Figure 1b of the manuscript, we can estimate the size of our QDs. We assume that they have a cylindrical shape, with a radius R, determined by the QD fabrication parameters, and thickness L = 6 nm, the same of the original QW, since it is reasonable that hydrogen is uniformly removed all along the thickness of the GaAs/GaAsN/GaAs QW. Since the emission energy, E, of an exciton in a QW of thickness L and in a cylindrical QD of thickness L and radius R are respectively

$$E^{\rm QW} = E_{\rm g} + E_{\rm L} - E_{\rm b}^{\rm QW}$$

and

$$E^{\rm QD} = E_{\rm g} + E_{\rm L} + E_{\rm R} - E_{\rm b}^{\rm QD}$$

where E_g is the energy gap, E_L and E_R are the confinement energies along the z-direction and radial direction, respectively. E_b^{QD} and E_b^{QW} are the (positive) exciton binding energies for the QD and QW, respectively. The difference between these two emission energies is given by

$$\Delta E = E_{\rm R} - \left(E_{\rm b}^{\rm QD} - E_{\rm b}^{\rm QW}\right).$$

 ΔE is experimentally determined by the data in Figure 1b of the manuscript, between the QD and QW exciton emissions.

The expression for E_R as a function of R is given by [1]

$$E_{\rm R} = b \frac{\hbar^2 u_{mp}^2}{2m^* R^2}$$

where u_{mp} is the *p*-th zeros of the *m*-th Bessel function (J_m) and $m^* = 0.14 m_0$ is the GaAsN electron effective mass $(m_0 \text{ being the electron mass})$ [2,3]. We are interested in the lowest energy level, where $u_{01} \approx 2.4048$. *b* is a factor to take into account the finite barrier (about 245 meV for the electrons) around the dot. Assuming *b* is the same of the *z*-direction, we have b = 0.63, which is given by the ratio of the electron confinement energies calculated for the GaAs/GaAsN/GaAs QW with finite and infinite potential barriers. We are neglecting the hole confinement contribution since the holes are subjected to a much smaller confinement

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potential (about 7 meV) [4] with respect to the electrons and its value is within our uncertainty.

The lowest energy exciton (formed by an electron and a light hole for every kind of GaAsN nanostructure [5,6,7]) in a QW like ours has been demonstrated to have about $E_b^{QW} = 10$ meV [8]. However, no calculation or data exist in the literature for the E_b^{QD} . Considering the E_b^{QD} in other III-V systems [9], we have assumed $E_b^{QD} = (20 \pm 10)$ meV.

The QD diameter, 2R, has therefore been calculated with the formula

$$2R = \sqrt{\frac{2b\hbar^2 u_{01}^2}{m^* (\Delta E + E_{\rm b}^{\rm QD} - E_{\rm b}^{\rm QW})}}$$

Considering the ΔE values 140, 125, 80, 30, 10 meV, corresponding to 0.7, 0.8, 0.9, 1.0 and 1.1 mW fabrication power and 1 s time exposure, we obtain 2R = 4.8, 5.0, 6.1, 9.2, 13 nm, respectively, with an error of about $\pm 15\%$. This proves that with the SNOM tip we have removed hydrogen from an area much smaller than the diffraction limit.

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